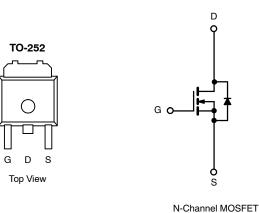
# N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (Ω)</b>	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
30	0.016 at V <sub>GS</sub> = 10 V	50 <sup>d</sup>	21.7			
30	0.022 at V <sub>GS</sub> = 4.5 V	50 <sup>d</sup>	21.7			



#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET ٠
- 100  $\%~R_{q}$  and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Power Supply
- Secondary Synchronous Rectification
- DC/DC Converter

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	v
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>1</sub> = 150 °C)	T <sub>C</sub> = 25 °C	1-	50 <sup>d</sup>	
Continuous Drain Current (1) = 150°C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	50 <sup>d</sup>	^
Pulsed Drain Current		I <sub>DM</sub>	100	A
Avalanche Current		I <sub>AS</sub>	40	
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	80	mJ
	T <sub>C</sub> = 25 °C	Р	59.5 <sup>b</sup>	14/
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	– P <sub>D</sub> –	2.7	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	46	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	2.1	0/10		

Notes:

a. Duty cycle  $\leq$  1 %.

b. See SOA curve for voltage derating.c. When mounted on 1" square PCB (FR-4 material).

d. Package limited.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static						•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	30			v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1		2.5	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			50	μΑ	
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$			250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-State Resistance <sup>a</sup>	Р	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22 A		0.011	0.016		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.015	0.022	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		110		S	
Dynamic <sup>b</sup>						•	
Input Capacitance	C <sub>iss</sub>			2780		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1 MHz		641			
Reverse Transfer Capacitance	C <sub>rss</sub>			260			
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		44	66		
Iotal Gale Charge				21.7	32.6	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 4.5 V, $I_D$ = 20 A		7			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			6.7			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.4	2	4	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	16		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, \text{ R}_{\text{I}} = 1.5 \Omega$		9	18		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10$ Å, $V_{GEN} = 10$ V, $R_g = 1$ $\Omega$		35	53	- ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			9	18		
Drain-Source Body Diode Ratings a	nd Characteris	stics T <sub>C</sub> = 25 °C <sup>b</sup>			-1		
Continuous Current	۱ <sub>S</sub>				50		
Pulsed Current	I <sub>SM</sub>				100	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		0.75	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			34	51	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 10 A, dl/dt = 100 A/μs		2	3	А	
Reverse Recovery Charge	Q <sub>rr</sub>			34	51	nC	

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

100

80

60

40

20

0

5

4

3

2

1

0 0.0

0.6

I<sub>D</sub> - Drain Current (A)

0.0

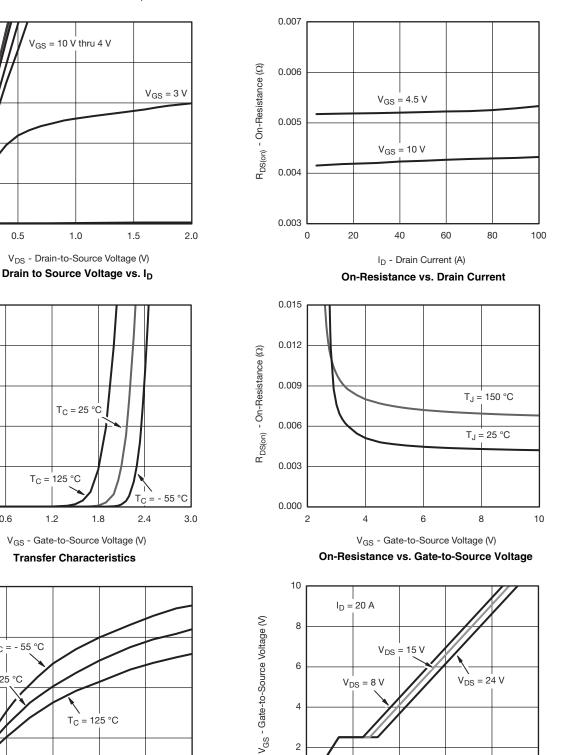
0.5

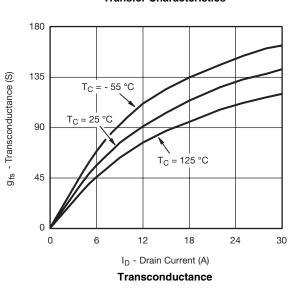
I<sub>D</sub> - Drain Current (A)

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

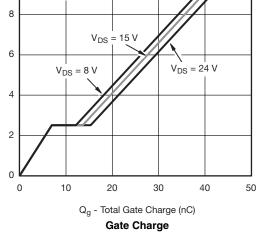
1.0





T<sub>C</sub> = 125 °C

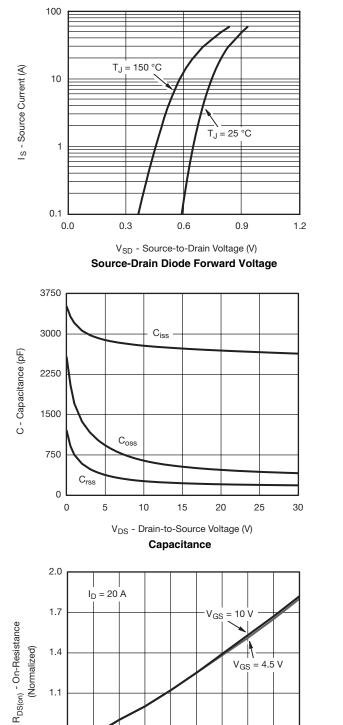
1.2

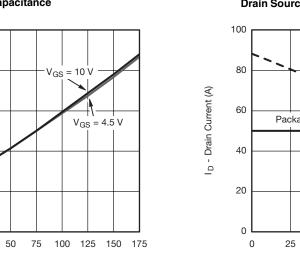


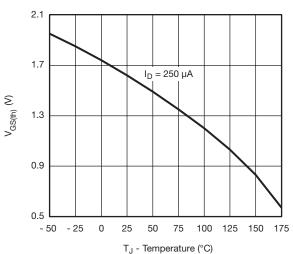
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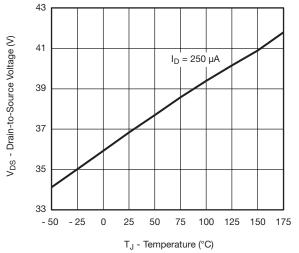
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

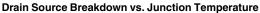


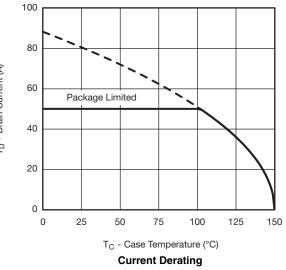




Threshold Voltage







0.8

0.5

- 50 - 25

0 25

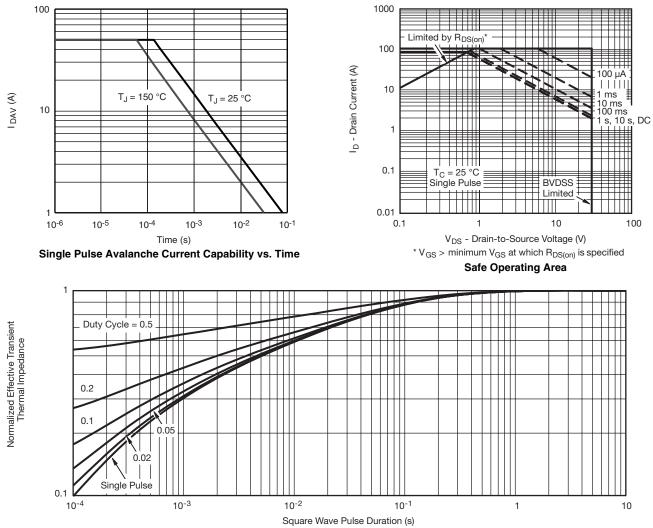
 $T_J$  - Junction Temperature (°C)

**On-Resistance vs. Junction Temperature** 



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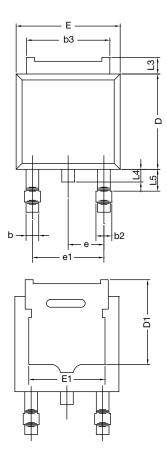
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case









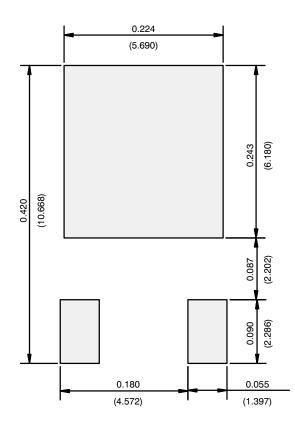
	MILLIN	IETERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
А	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28 BSC		0.090 BSC			
e1	4.56	56 BSC 0.180 BSC		4.56 BSC		) BSC
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12- DWG: 534	0247-Rev. M,	24-Dec-12				

Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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